

Description

The AST24CL is a Bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The AST24CL complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into a lead-free SOT-323 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

• Protects two Bi-directional lines

Ultra low leakage: nA level

Operating voltage: 24V

Complies with following standards:

- IEC 61000-4-2 (ESD) immunity test

Air discharge: ±25kV Contact discharge: ±20kV

– IEC61000-4-5 (Lightning) 3A (8/20μs)

RoHS Compliant

Mechanical Characteristics

Package: SOT-323Lead Finish: Matte Tin

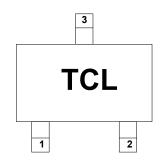
Case Material: "Green" Molding Compound.Terminal Connections: See Diagram Below

Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Notebooks and Handhelds
- Portable Instrumentation
- Set Top Box
- Industrial Controls
- Server and Desktop PC

Marking Information



Ordering Information

Dimensions and Pin Configuration

Part Number	Packaging	Reel Size
AST24CL	3000/Tape & Reel	7 inch

www.appliedpowermicro.com



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

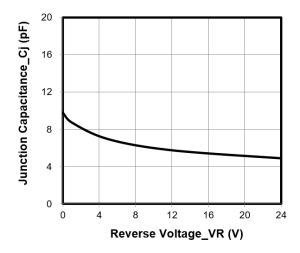
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	150	W
Peak Pulse Current (8/20μs)	IPP	3	А
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	VESD	±25 ±20	kV
Operating Temperature Range	TJ	-55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

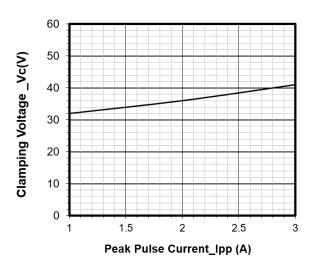
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			24	V	
Breakdown Voltage	VBR	27			V	IT = 1mA
Reverse Leakage Current	I _R			0.2	μΑ	VRWM = 24V
Clamping Voltage	Vc			36	V	IPP = 1A (8 x 20µs pulse)
Clamping Voltage	Vc			50	V	IPP = 3A (8 x 20µs pulse)
Junction Capacitance	Сл		10		pF	VR = 0V, f = 1MHz, Pin 1 to Pin 3 or Pin 2 to Pin 3
Junction Capacitance	CJ		5		pF	VR = 0V, f = 1MHz, Pin 1 to Pin 2



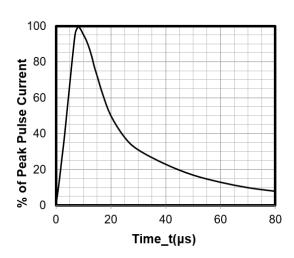
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



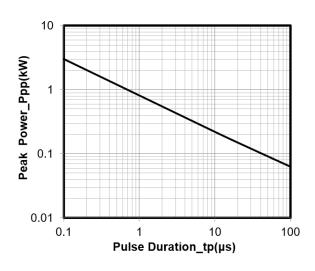
Junction Capacitance vs. Reverse Voltage



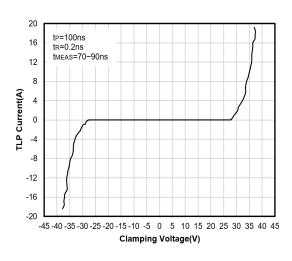
Clamping Voltage vs. Peak Pulse Current



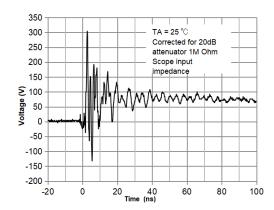
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



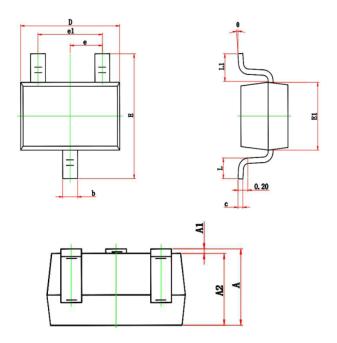
TLP Curve



Note: Data is taken with a 10x attenuator ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

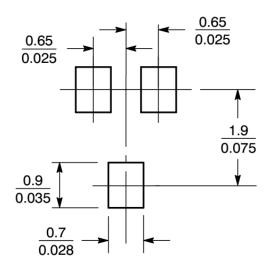


SOT-323 Package Outline Drawing



C 1 1	Dim in mm				
Symbol	Min	Nor	Max		
A	0. 90	1.00	1. 10		
A1	0.00	0.05	0. 10		
A2	0. 90	0.95	1.00		
b	0. 20	0.30	0.40		
c	0.08	0.12	0. 15		
D	2.00	2. 10	2. 20		
Е	2. 15	2.30	2. 45		
E1	1. 15	1. 25	1. 35		
е	0. 650TPY.				
e1	1.2	1.3	1.4		
L	0. 26	0.36	0.46		
L1	0. 525REF.				
θ	0°	4°	8°		

Suggested Land Pattern



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